

EDB10XS SERIES

SUPER FAST SURFACE MOUNT SILICON BRIDGE RECTIFIER

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EDB101S THRU EDB106S

SINGLE-PHASE GLASS PASSIVATED SUPER FAST SURFACE MOUNT SILICON BRIDGE RECTIFIER



康比電子
HORNBY ELECTRONIC

REVERSE VOLTAGE: 50 to 400 VOLTS
FORWARD CURRENT: 1.0 AMPERE

FEATURES

- Glass passivated chip junction
- Superfast recovery times for high efficiency
- High surge overload rating of 50 Amperes peak
- Ideal for printed circuit board
- High temperature soldering guaranteed:
260°C for 10 seconds

MECHANICAL DATA

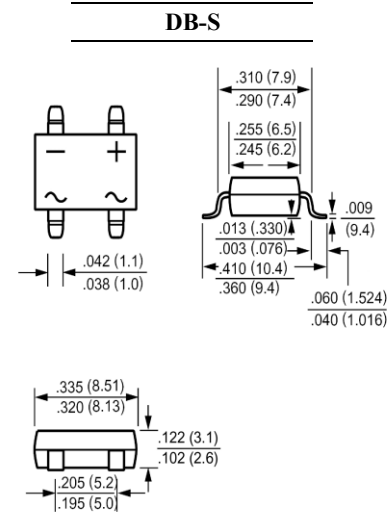
Case: Molded plastic, DB-S

Epoxy: UL 94V-O rate flame retardant

Terminals: Leads solderable per MIL-STD-202,
method 208 guaranteed

Mounting position: Any

Weight: 0.02ounce, 0.4gram



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

	Symbols	EDB101S	EDB102S	EDB103S	EDB104S	EDB105S	EDB106S	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	Volts
Maximum RMS Voltage	V_{RMS}	35	70	105	140	210	280	Volts
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	Volts
Maximum Average Forward Rectified Current at $T_A=40$	$I_{(AV)}$	1.0						Amp
Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	50						Amp
Maximum Forward Voltage at 1.0A DC and 25	V_F	1.05				1.25		Volts
Maximum Reverse Current at $T_A=25$ at Rated DC Blocking Voltage $T_A=125$	I_R	5.0				1000		uAmp
Typical Junction Capacitance (Note 1)	C_J	15						pF
Maximum Reverse Recovery Time (Note 3)	T_{RR}	50						nS
Typical Thermal Resistance (Note 2)	$R_{\theta JA}$	38						/W
Typical Thermal Resistance (Note 2)	$R_{\theta JL}$	12						/W
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150						

NOTES:

1- Measured at 1 MHz and applied reverse voltage of 4.0 VDC.

2- Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.5 x 0.5" (13 x 13mm) copper pads

3- Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1A$, $I_{RR}=0.25A$.

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RATINGS AND CHARACTERISTIC CURVES

Fig. 1 - Derating Curve Output Rectified Current

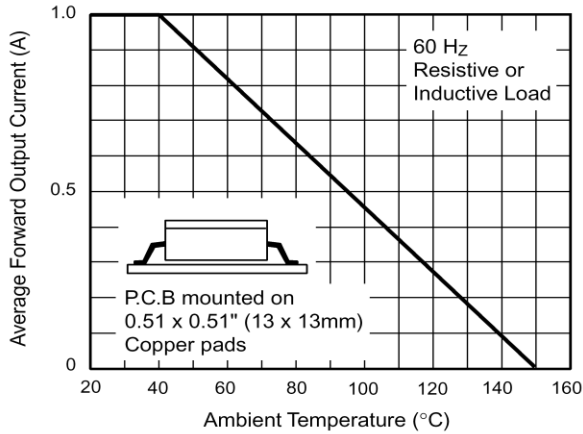


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

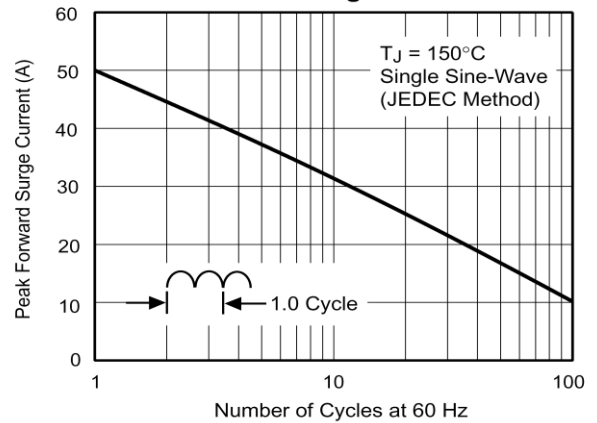


Fig. 3 - Typical Forward Characteristics Per Leg

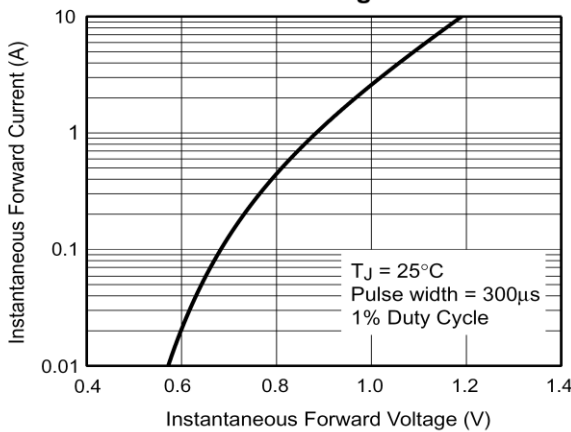


Fig. 4 - Typical Reverse Leakage Characteristics Per Leg

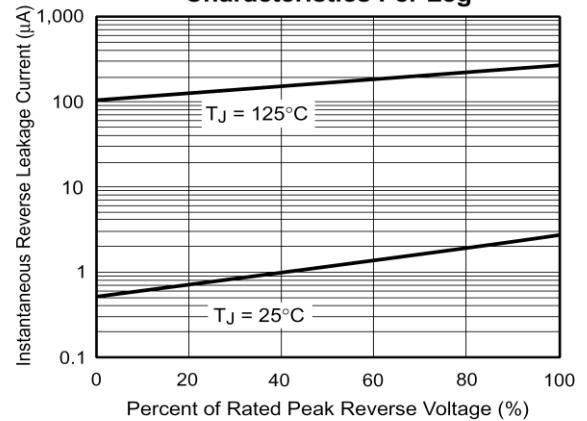


Fig. 5 - Typical Junction Capacitance Per Leg

